

region with a second semiconductor material, wherein the first and second semiconductor materials are different semiconductor materials.

16. The method of claim 15, wherein the forming comprises:

providing at least one cavity in the substrate; and epitaxially growing the second semiconductor material from one or more surfaces of the at least one cavity to form the at least one region.

17. The method of claim 13, further comprising forming, before the fabricating, multiple fins extending from the substrate, wherein the fabricating comprises fabricating at least one region of the first p-type region, first n-type region, second p-type region, or second n-type region to comprise one or more fins of the multiple fins of the substrate.

18. The structure of claim 1, wherein the first n-type region is disposed directly within the n-type well of the substrate, and wherein the second p-type region is disposed directly within the p-type well of the substrate.

19. The structure of claim 1, wherein the first p-type region and the first n-type region are spaced from one another, and wherein the second p-type region and the second n-type region are spaced from one another.

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